



PTO/SB/21 (09-04)

**TRANSMITTAL  
FORM**

(to be used for all correspondence after initial filing)

Total Number of Pages in This Submission

16

Application Number

10/666,034

Filing Date

September 18, 2003

First Named Inventor

Kocon, Christopher Boguslaw

Art Unit

2814

Examiner Name

Long Pham

Attorney Docket Number

018865-009010US

**ENCLOSURES (Check all that apply)**

Fee Transmittal Form



Fee Attached



Amendment/Reply



After Final



Affidavits/declaration(s)



Extension of Time Request



Express Abandonment Request



Information Disclosure Statement



Drawing(s)



Licensing-related Papers



Petition

Petition to Convert to a  
Provisional ApplicationPower of Attorney, Revocation  
Change of Correspondence Address

Terminal Disclaimer



Request for Refund



CD, Number of CD(s) \_\_\_\_\_



Landscape Table on CD



After Allowance Communication to TC

Appeal Communication to Board  
of Appeals and InterferencesAppeal Communication to TC  
(Appeal Notice, Brief, Reply Brief)

Proprietary Information



Status Letter

Other Enclosure(s) (please identify  
below):

Return Postcard

PTO/SB/08A &amp; PTO/SB/08B

82 Reference Copies

Certified Copy of Priority  
Document(s)Reply to Missing Parts/ Incomplete  
ApplicationReply to Missing Parts  
under 37 CFR 1.52 or 1.53

Remarks

The Commissioner is authorized to charge any additional fees to Deposit  
Account 20-1430.Total number of pages does not include cited references.**SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT**

Firm Name

Townsend and Townsend and Crew LLP

Signature

Printed name

Barmak Sani

Date

March 17, 2005

Reg. No.

45,068

**CERTIFICATE OF TRANSMISSION/MAILING**

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Tiffany Wu

Date

March 17, 2005



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PATENT  
Attorney Docket No.: 018865-009010US  
Client Reference No.: 17732.51620.003

On 3/17/05

TOWNSEND and TOWNSEND and CREW LLP

By: [Signature]  
Tiffany Wu

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:

Christopher Boguslaw Kocon

Application No.: 10/666,034

Filed: September 18, 2003

For: METHOD FOR FORMING A  
SEMICONDUCTOR STRUCTURE  
WITH IMPROVED SMALLER  
FORWARD VOLTAGE LOSS AND  
HIGHER BLOCKING CAPABILITY

Examiner: Long Pham

Art Unit: 2814

INFORMATION DISCLOSURE  
STATEMENT UNDER 37 CFR §1.97 and  
§1.98

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

03/22/2005 HTECKLU1 00000041 201430 10666034

01 FC:1806 180.00 DA

Sir:

The references cited on attached form PTO/SB/08A and PTO/SB/08B are being called to the attention of the Examiner. Copies of the Foreign Patents and Non Patent Literature references are enclosed. It is respectfully requested that the cited references be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

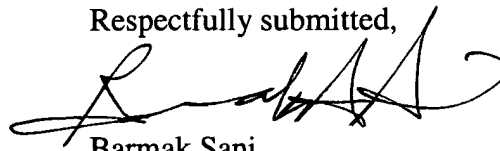
As provided for by 37 CFR 1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no

representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information.

This IDS is being filed before the mailing date of the final Office Action or Notice of Allowance.

Please charge the IDS fee of \$180 to Deposit Account No. 20-1430. Please deduct any additional fees from, or credit any overpayment to, the above-noted Deposit Account.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Barmak Sani', with a stylized flourish at the end.

Barmak Sani  
Reg. No. 45,068

TOWNSEND and TOWNSEND and CREW LLP  
Two Embarcadero Center, Eighth Floor  
San Francisco, California 94111-3834  
Tel: 650-326-2400  
Fax: 650-326-2422  
BSS:ewm  
60436135 v1



<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			<b>Complete if Known</b>		
			Application Number	10/666,034	
			Filing Date	September 18, 2003	
			First Named Inventor	Kocon, Christopher Boguslaw	
			Art Unit	2814	
			Examiner Name	Long Pham	
Sheet	1	of	12	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US-3,404,295	10-01-1968	Warner et al.	
	2	US-3,412,297	11-19-1968	Amlinger	
	3	US-3,497,777	02-24-1970	Teszner et al.	
	4	US-3,564,356	02-16-1971	Wilson	
	5	US-3,660,697	05-02-1972	Berglund et al.	
	6	US-4,003,072	01-11-1977	Matsushita et al.	
	7	US-4,300,150	11-10-1981	Colak	
	8	US-4,326,332	04-27-1982	Kenney et al.	
	9	US-4,337,474	06-29-1982	Yukimoto	
	10	US-4,345,265	08-17-1982	Blanchard	
	11	US-4,445,202	04-24-1984	Geotze et al.	
	12	US-4,579,621	04-01-1986	Hine	
	13	US-4,636,281	01-13-1987	Buiguez et al.	
	14	US-4,638,344	01-20-1987	Cardwell, Jr.	
	15	US-4,639,761	01-27-1987	Singer et al.	
	16	US-4,698,653	10-06-1987	Cardwell, Jr.	
	17	US-4,716,126	12-29-1987	Cogan	
	18	US-4,746,630	05-24-1988	Hui et al.	
	19	US-4,754,310	06-28-1988	Coe	
	20	US-4,774,556	09-27-1988	Fujii et al.	
	21	US-4,801,986	01-31-1989	Chang et al.	
	22	US-4,821,095	04-11-1989	Temple	
	23	US-4,823,176	04-18-1989	Baliga et al.	
	24	US-4,853,345	08-01-1989	Himelick	
	25	US-4,868,624	09-19-1989	Grung et al.	
	26	US-4,893,160	01-09-1990	Blanchard	
	27	US-4,914,058	04-03-1990	Blanchard	
	28	US-4,941,026	07-10-1990	Temple	
	29	US-4,967,245	10-30-1990	Cogan et al.	
	30	US-4,969,028	11-06-1990	Baliga	
	31	US-4,974,059	11-27-1990	Kinzer	
	32	US-4,990,463	02-05-1991	Mori	
	33	US-4,992,390	02-12-1991	Hsueh-Rong Chang	
	34	US-5,027,180	06-25-1991	Nishizawa et al.	
	35	US-5,034,785	07-23-1991	Blanchard	
	36	US-5,071,782	12-10-1991	Mori	
	37	US-5,072,266	12-10-1991	Buluccea	
	38	US-5,079,608	01-07-1992	Wodarczyk et al.	
	39	US-5,105,243	04-14-1992	Nakagawa et al.	
	40	US 5,111,253	05-05-1992	Korman et al.	
	41	US-5,142,640	08-25-1992	Iwanatsu	
Examiner Signature			Date Considered		

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60436135 v1

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			Art Unit	2814	
			Examiner Name	Long Pham	
Sheet	2	of	12	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code <sup>2</sup> (if known)			
	42	US-5,164,325	11-17-1992	Cogan et al.	
	43	US-5,164,802	11-17-1992	Jones et al.	
	44	US-5,216,275	06-01-1993	Chen	
	45	US-5,219,777	06-15-1993	Kang	
	46	US-5,219,793	06-15-1993	Cooper et al.	
	47	US-5,233,215	08-03-1993	Baliga	
	48	US-5,262,336	11-16-1993	Pike, Jr. et al.	
	49	US-5,268,311	12-07-1993	Euen et al.	
	50	US-5,275,965	01-04-1994	Manning	
	51	US-5,294,824	03-15-1994	Okada	
	52	US-5,298,761	03-29-1994	Cogan et al.	
	53	US-5,300,447	04-05-1994	Anderson	
	54	US-5,326,711	07-05-1994	Malhi	
	55	US-5,350,937	09-27-1994	Yamazaki et al.	
	56	US-5,365,102	11-15-1994	Mehrotra et al.	
	57	US-5,366,914	11-22-1994	Takahashi et al.	
	58	US-5,389,815	02-14-1995	Takahashi	
	59	US-5,405,794	04-11-1995	Kim	
	60	US-5,418,376	05-23-1995	Muraoka et al.	
	61	US-5,424,231	06-13-1995	Yang	
	62	US-5,429,977	07-04-1995	Lu et al.	
	63	US-5,430,311	07-04-1995	Murakami et al.	
	64	US-5,430,324	07-04-1995	Bencuya	
	65	US-5,436,189	07-25-1995	Beasom	
	66	US-5,438,215	08-01-1995	Tihanyi	
	67	US-5,442,214	08-15-1995	Yang	
	68	US-5,454,435	07-18-1995	Baliga	
	69	US-5,473,176	12-05-1995	Kakumoto	
	70	US-5,473,180	12-05-1995	Ludikhuizen	
	71	US-5,474,943	12-12-1995	Hsieh et al.	
	72	US-5,519,245	05-21-1996	Tokura et al.	
	73	US-5,541,425	07-30-1996	Nishihara	
	74	US-5,554,862	09-10-1996	Omura et al.	
	75	US-5,567,634	10-22-1996	Hebert et al.	
	76	US-5,567,635	10-22-1996	Acovic et al.	
	77	US-5,572,048	11-05-1996	Sugawara	
	78	US-5,576,245	11-19-1996	Cogan et al.	
	79	US-5,578,851	11-26-1996	Hsieh et al.	
	80	US-5,581,100	12-03-1996	Ajit	
	81	US-5,583,065	12-10-1996	Miwa	
	82	US-5,592,005	01-07-1997	Floyd et al.	
Examiner Signature				Date Considered	

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>	
			Application Number	10/666,034
			Filing Date	September 18, 2003
			First Named Inventor	Kocon, Christopher Boguslaw
			Art Unit	2814
Examiner Name	Long Pham			
Sheet <b>3</b>	of	<b>12</b>	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	83	US-5,595,927	01-21-1997	Chen et al.	
	84	US-5,597,765	01-28-1997	Yilmaz et al.	
	85	US-5,605,852	02-25-1997	Bencuya	
	86	US-5,616,945	04-01-1997	Williams	
	87	US-5,623,152	04-22-1997	Majumdar et al.	
	88	US-5,629,543	05-13-1997	Hshieh et al.	
	89	US-5,637,898	06-10-1997	Baliga	
	90	US-5,639,676	06-17-1997	Hshieh et al.	
	91	US-5,640,034	07-17-1997	Satwinder Malhi	
	92	US-5,648,670	07-15-1997	Blanchard	
	93	US-5,656,843	08-12-1997	Goodyear et al.	
	94	US-5,665,619	09-09-1997	Kwan et al.	
	95	US-5,670,803	09-23-1997	Beilstein, Jr. et al.	
	96	US-5,689,128	11-18-1997	Hshieh et al.	
	97	US-5,693,569	12-02-1997	Ueno	
	98	US-5,705,409	01-06-1998	Witek	
	99	US-5,710,072	01-20-1998	Krautschneider et al.	
	100	US-5,714,781	02-03-1998	Yamamoto et al.	
	101	US-5,719,409	02-17-1998	Singh et al.	
	102	US-5,744,372	04-28-1998	Bulucea	
	103	US-5,770,878	06-23-1998	Beasom	
	104	US-5,776,813	07-07-1998	Huang et al.	
	105	US-5,780,343	07-14-1998	Bashir	
	106	US-5,801,417	09-01-1998	Tsang et al.	
	107	US-5,814,858	09-29-1998	Williams	
	108	US-5,877,528	03-02-1999	So	
	109	US-5,879,971	03-09-1999	Witek	
	110	US-5,879,994	03-09-1999	Kwan et al.	
	111	US-5,895,951	04-20-1999	So et al.	
	112	US-5,895,952	04-20-1999	Darwish et al.	
	113	US-5,897,343	04-27-1999	Mathew et al.	
	114	US-5,897,360	04-27-1999	Kawaguchi	
	115	US-5,900,663	05-04-1999	Johnson et al.	
	116	US-5,906,680	05-25-1999	Meyerson	
	117	US-5,917,216	06-29-1999	Floyd et al.	
	118	US-5,929,481	07-27-1999	Hsieh et al.	
	119	US-5,943,581	08-24-1999	Lu et al.	
	120	US-5,949,104	09-07-1999	D'Anna et al.	
	121	US-5,949,124	09-07-1999	Hadizad et al.	
	122	US-5,959,324	09-28-1999	Kohyama	
	123	US-5,960,271	09-28-1999	Wollesen et al.	

Examiner Signature	Date Considered
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60436135 v1

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Sheet	4	of	12	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
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		Number Kind Code <sup>2</sup> (* known)			
	124	US-5,972,741	10-26-1999	Kubo et al.	
	125	US-5,973,360	10-26-1999	Tihanyi	
	126	US-5,973,367	10-26-1999	Williams	
	127	US-5,976,936	11-02-1999	Miyajima et al.	
	128	US-5,981,344	11-09-1999	Hshieh et al.	
	129	US-5,981,996	11-09-1999	Fujishima	
	130	US-5,998,833	12-07-1999	Baliga	
	131	US-6,005,271	12-21-1999	Hshieh	
	132	US-6,008,097	12-28-1999	Yoon et al.	
	133	US-6,011,298	01-04-2000	Blanchard	
	134	US-6,015,727	01-18-2000	Wanlass	
	135	US-6,020,250	02-01-2000	Kenny et al.	
	136	US-6,034,415	05-07-2000	Johnson et al.	
	137	US-6,037,202	03-14-2000	Witek	
	138	US-6,037,628	03-14-2000	Huang	
	139	US-6,037,632	03-14-2000	Omura et al.	
	140	US-6,040,600	03-21-2000	Uenishi et al.	
	141	US-6,048,772	04-11-2000	D'Anna	
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	143	US-6,057,558	05-02-2000	Yamamoto et al.	
	144	US-6,063,678	05-16-2000	D'Anna	
	145	US-6,064,088	05-16-2000	D'Anna	
	146	US-6,066,878	05-23-2000	Neilson	
	147	US-6,069,043	05-30-2000	Floyd et al.	
	148	US-6,081,009	06-27-2000	Neilson	
	149	US-6,084,264	07-04-2000	Darwish	
	150	US-6,084,268	07-04-2000	de Frésart et al.	
	151	US-6,087,232	07-11-2000	Kim et al.	
	152	US-6,096,608	08-01-2000	Williams	
	153	US-6,097,063	08-01-2000	Fujihira	
	154	US-6,103,578	08-15-2000	Uenishi et al.	
	155	US-6,104,054	08-15-2000	Corsi et al.	
	156	US-6,110,799	08-29-2000	Huang	
	157	US-6,114,727	09-05-2000	Ogura et al.	
	158	US-6,137,152	10-24-2000	Wu	
	159	US-6,150,697	11-21-2000	Teshigahara et al.	
	160	US-6,156,606	12-05-2000	Michaelis	
	161	US-6,156,611	12-05-2000	Lan et al.	
	162	US-5,168,973	12-08--1992	Asayama et al.	
	163	US-6,163,052	12-19-2000	Liu et al.	
	164	US-6,165,870	12-26-2000	Shim et al.	

Examiner Signature	Date Considered
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	165	US-6,168,983	01-02-2001	Rumennik et al.	
	166	US-6,168,996	01-02-2001	Numazawa et al.	
	167	US-6,171,935	01-09-2001	Nance et al.	
	168	US-6,174,773	01-16-2001	Fujishima	
	169	US-6,174,785	01-16-2001	Parekh et al.	
	170	US-6,184,545	02-06-2001	Werner et al.	
	171	US-6,184,555	02-06-2001	Tihanyi et al.	
	172	US-6,188,104	02-13-2001	Choi et al.	
	173	US-6,188,105	02-13-2001	Kocon et al.	
	174	US-6,190,978	02-20-2001	D'Anna	
	175	US-6,191,447	02-20-2001	Baliga	
	176	US-6,194,741	02-27-2001	Kinzer et al.	
	177	US-6,198,127	03-06-2001	Kocon	
	178	US-6,201,279	03-13-2001	Pfirsch	
	179	US-6,204,097	03-20-2001	Shen et al.	
	180	US-6,207,994	03-27-2001	Rumennik et al.	
	181	US-6,222,233	04-24-2001	D'Anna	
	182	US-6,225,649	05-01-2001	Minato	
	183	US-6,228,727	05-08-2001	Lim et al.	
	184	US-6,239,463	05-29-2001	Williams et al.	
	185	US-6,239,464	05-29-2001	Tsuchitani et al.	
	186	US-6,265,269	07-24-2001	Chen et al.	
	187	US-6,271,100	08-07-2001	Ballantine et al.	
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	205	US-6,337,499	01-08-2002	Werner	

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			Application Number	10/666,034	
			Filing Date	September 18, 2003	
			First Named Inventor	Kocon, Christopher Boguslaw	
			Art Unit	2814	
Examiner Name	Long Pham				
Sheet	6	of	12	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code <sup>2</sup> (if known)			
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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

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**Complete if Known**

Application Number	10/666,034
Filing Date	September 18, 2003
First Named Inventor	Kocon, Christopher Boguslaw
Art Unit	2814
Examiner Name	Long Pham
Attorney Docket Number	018865-009010US

## U.S. PATENT DOCUMENTS+

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## FOREIGN PATENT DOCUMENTS

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		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
	259	CN	1036666A		10-25-1989			<input checked="" type="checkbox"/>
	260	DE	4300806	C1	12-23-1993	Siemens AG		<input checked="" type="checkbox"/>
	261	DE	19736981	A1	08-20-1998	Mitsubishi Denki		<input checked="" type="checkbox"/>
	262	EP	0747967	B1	02-27-2002	ST Microelectronics Inc.		<input type="checkbox"/>
	263	EP	0975024	A2	01-02-2000	Fuji Electric Co. LTD.		<input type="checkbox"/>
	264	EP	1026749	A1	08-09-2000	Mitsubishi Denki Kabushiki		<input type="checkbox"/>
	265	EP	1054451	A2	11-22-2000	Intersil Corporation		<input type="checkbox"/>
	266	EP	1205960	A1	05-15-2002	Infineon Technologies AG		<input type="checkbox"/>
	267	JP	01-192174	A	08-02-1989	Hitachi LTD.		<input checked="" type="checkbox"/>
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	269	JP	56-058267	A	05-21-1981	Nippon Telegr & Teleph Corp.		<input checked="" type="checkbox"/>
	270	JP	62-069562		03-30-1987	Mitsubishi Electric Corp		<input checked="" type="checkbox"/>
	271	JP	63-186475		08-02-1988	Nissan Motor Co. LTD.		<input checked="" type="checkbox"/>
	272	JP	63-288047		11-25-1988	Toshiba Corp.		<input checked="" type="checkbox"/>
	273	JP	64-022051		01-25-1989	Matsushita Electric Ind		<input checked="" type="checkbox"/>
	274	JP	2000-040822		02-08-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	275	JP	2000-040872		02-08-2000	Senju Metal IND CO LTD.		<input checked="" type="checkbox"/>
	276	JP	2000-156978	A	06-06-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	277	JP	2000-277726	A	10-06-2000	Toshiba Corp.		<input checked="" type="checkbox"/>
	278	JP	2000-277728	A	10-06-2000	NEC Kansai LTD.		<input checked="" type="checkbox"/>
	279	JP	2001-015448		01-19-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	280	JP	2001-015752		01-19-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	281	JP	2001-102577	A	04-13-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	282	JP	2001-111041	A	04-20-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	283	JP	2001-135819	A	05-18-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	284	JP	2001-144292	A	05-25-2001	Denso Corp.		<input checked="" type="checkbox"/>
	285	JP	2001-244461	A	09-07-2001	Toyota Central Res & Dev Lab INC.		<input checked="" type="checkbox"/>
	286	JP	2001-313391	A	12-20-2001	S. Takahiro et al.		<input checked="" type="checkbox"/>
	287	JP	2002-083976	A	03-22-2002	Naito et al.		<input checked="" type="checkbox"/>
	288	PCT	WO 00/33386	A2	06-08-2000	Koninklijke Philips Electronics		<input type="checkbox"/>
	289	PCT	WO 00/68997	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	290	PCT	WO 00/68998	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	291	PCT	WO 00/75965	A2	12-14-2000	General Semiconductor, Inc.		<input type="checkbox"/>
	292	PCT	WO 01/06550	A1	01-23-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	293	PCT	WO 01/06557	A1	01-25-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	294	PCT	WO 01/45155	A1	06-21-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	295	PCT	WO 01/59847	A2	08-16-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	296	PCT	WO 01/71815		09-27-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	297	PCT	WO 01/95385	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>

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			First Named Inventor	Kocon, Christopher Boguslaw	
			Art Unit	2814	
			Examiner Name	Long Pham	
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	298	PCT	WO 01/95398	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>
	299	PCT	WO 02/01644	A2	01-03-2002	Silicon Wireless Corporation		<input type="checkbox"/>
	300	PCT	WO 02/047171	A1	06-13-2002	International Rectifier Corporation		<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>

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	318	KAO et al. "Two Dimensional Thermal Oxidation of Silicon-I. Experiments," <u>IEEE Transactions on Electron Devices</u> , Vol. ED-34, No. 5, May 1987, pp. 1008-1017.	
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	320	KASSAKIAN, J.G. et al., "High-frequency high-density converters for distributed power supply systems," (April, 1988) <i>Proceedings of the IEEE</i> , Vol. 76, No. 4, pp. 362-376.	
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Sheet	12	of	12	Attorney Docket Number	018865-009010US

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>	
	333	Technical Literature from Quester Technology, Model APT-4300 300mm Atmospheric TEOS/Ozone CVD System, (unknown date), 3 pages total.		
	334	Technical Literature from Quester Technology, Model APT-6000 Atmospheric TEOS-Ozone CVD System, (unknown date), 2 pages total.		
	335	Technical Literature from Silicon Valley Group Thermal Systems, APNext, High Throughput APCVD Cluster Tool for 200 mm/300 mm Wafer Processing, (unknown date), 2 pages total.		
	336	TU et al. "On the reverse blocking characteristics of schottky power diodes," (December 1992) <i>IEEE Transactions on Electron Devices</i> . Vol. 39, No. 12, pp. 2813-2814 2 pages total.		
	337	UEDA et al. "An Ultra-Low On-Resistance Power MOSFET Fabricated by Using a Fully Self-Aligned Process," <i>IEEE Transactions on Electron Devices</i> 34:926-930 (1987).		
	338	WILAMOWSKI "Schottky Diodes with High Breakdown Voltages," <i>Solid-State Electronics</i> 26:491-493 (1983).		
	339	WOLF, "Silicon Processing for The VLSI Era" Vol. 2 Process Integration Lattice Press (1990), 3 pages total.		
	340	YAMASHITA et al., "Conduction Power loss in MOSFET synchronous rectifier with parallel-connected schottky barrier diode, (July 1998) <i>IEEE Transactions on Power electronics</i> , Vol. 13, No. 4, pp. 667-673.		

Examiner Signature		Date Considered	
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<sup>1</sup> EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.